

COMBINED DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that :

I believe I am the sole (if only one name appears below), or joint (if more than one name appears), original and first inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled :

"METHOD OF FABRICATING A MOS TRANSISTOR WITH A SHALLOW JUNCTION"

The specification for the above entitled invention is filed herewith.

The specification for the above entitled invention was filed previously

with application serial number: _____ Filing Date: _____

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to the patentability of the invention disclosed in this application in accordance with Title 37, Code of Federal Regulations, Section 1.56 (a). I further acknowledge the duty in any continuation-in-part application to disclose to the Patent and Trademark Office all information known to be material to the patentability of the invention disclosed in this application, as defined in 1.56, which became available to me between the filing date of the prior application and the filing date of this application.

PRIORITY CLAIM

There is no claim of priority

Claim of priority is based on the following:

POWER OF ATTORNEY

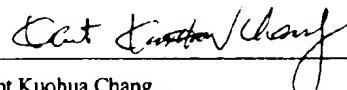
As a named inventor, I hereby appoint the following attorney to prosecute this application and to transact all related business in the Patent and Trademark Office:

Winston Hsu, Registration Number 41,526
5F, No.389, Fu-Ho Rd., YUNGHO City,
Taipei Hsien, Taiwan, R.O.C.
TEL: +886-2-8923-7350

DECLARATION

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued hereon.

Date: 10-05-2001



Printed Name: Kent Kuohua Chang
Post Office Address: 4F, No. 66-1, Yen-Chi St., Taipei City, Taiwan, R.O.C.
and Residence
Citizen of: R.O.C.

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As a below named inventor, I hereby declare that :

I believe I am the sole (if only one name appears below), or joint (if more than one name appears), original and first inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled :

"METHOD OF FABRICATING A MOS TRANSISTOR WITH LOW GATE DEPLETION"

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with application serial number: _____ Filing Date: _____

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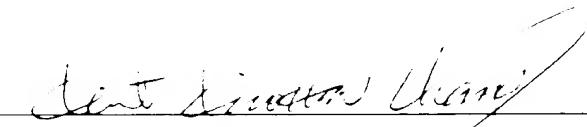
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Date: 12.15.01


Kent Kuohua Chang

Printed Name: Kent Kuohua Chang
Post Office Address: 4F, No. 66-1, Yen-Chi St., Taipei City, Taiwan, R.O.C.
and Residence
Citizen of: R.O.C

ASSIGNMENT OF INVENTION

I.(Assignor Name) Kent Kuohua Chang, residing at (Address)
4F, No. 66-1, Yen-Chi St., Taipei City, Taiwan, R.O.C.
have invented a device called

"METHOD OF FABRICATING A MOS TRANSISTOR WITH LOW GATE DEPLETION"

(Assignee name) Macronix International Co. Ltd.
(hereinafter 'Assignee'), of (Assignee address)
No.16, Li-Hsin Rd., Science-Based Industrial Park, Hsin-Chu, Taiwan, R.O.C.
wishes to acquire the entire right, title, and interest in and to the invention and to any letters patent that may be granted therefor in the United States and in any and all foreign countries.

Accordingly, in consideration of the sum of One Dollar, (\$1.00) to me in hand paid, the receipt of which is hereby acknowledged, and other good and valuable consideration, Assignor hereby sells, assigns, and transfers to Assignee the full and exclusive right to the above described invention in the United States and its territorial possessions, and in all foreign countries. The rights granted include the entire right, title, and interest in and to any and all letters patent which may be granted on the invention, including any rights gained by divisions, reissues, continuations, and extensions of the above described application.

I hereby authorize and request the Patent and Trademark Office Officials in the United States and any and all foreign countries to issue any and all letters patent, when issued, to Assignee, as the assignee of my entire right, title, and interest in and to the invention, for the sole use and enjoyment of Assignee and its successors and assignees.

Further, I agree that I will communicate to Assignee or its representatives any facts known to me respecting the invention, to testify in any legal proceedings, to sign all lawful papers, to execute all divisions, continuations, substitutions, renewal and reissue applications, and to generally do those things necessary to aid Assignee and its successors and assigns to obtain and enforce proper protection for the invention in the United States and in any and all foreign countries.

Date: 1-10-01.

(Assignor signature)

Kent Kuohua Chang

(Print Assignor's name)